

# Raman and XPS characterization of synthesized PtSe<sub>2</sub> thin films

Oliver Hartwig<sup>1</sup>

Maximilian Precht<sup>1</sup>, Sebastian Lukas<sup>2</sup>, Satender Kataria<sup>2</sup>, Kangho Lee<sup>1</sup>, Cormac Ó Coileáin<sup>1,3</sup>, Tanja Stimpel-Lindner<sup>1</sup>, Max Lemme<sup>2</sup>, Georg S. Duesberg<sup>1,3</sup>

<sup>1</sup> Institute of Physics, Universität der Bundeswehr München, Werner-Heisenberg-Weg 3, 85577 Neubiberg, Germany

<sup>2</sup> Chair of Electronic Devices, RWTH Aachen University, Otto-Blumenthal-Str. 2, 52074 Aachen, Germany

<sup>3</sup> Centre For Research on Nanostructure and Nanodevices, School of Chemistry, Trinity College Dublin, Dublin 2, Ireland

[oliver.hartwig@unibw.de](mailto:oliver.hartwig@unibw.de)

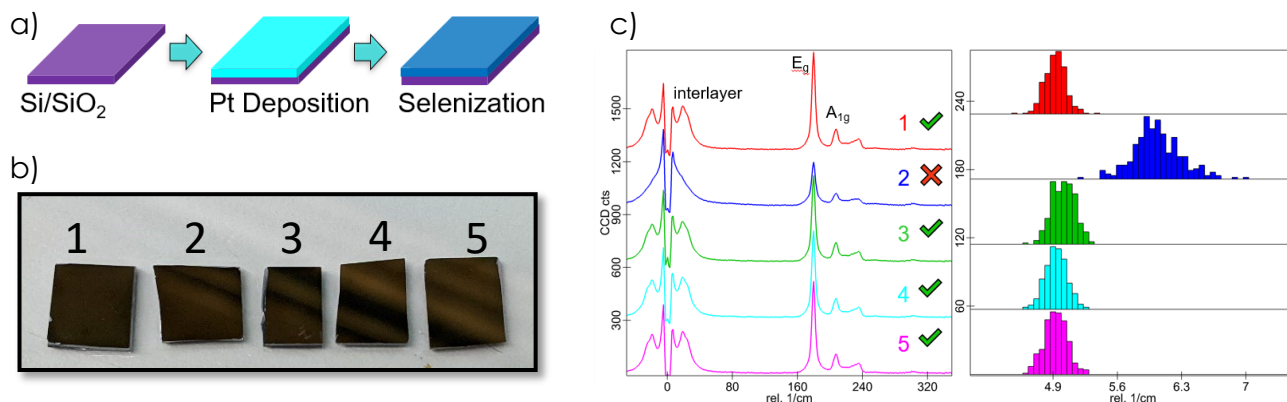
Platinumdiselenide (PtSe<sub>2</sub>) is a layered noble metal dichalcogenide (NMD) with a number of remarkable properties. The bulk semimetal undergoes a transition to semiconductor with decreasing number of atomic layers. Few layered PtSe<sub>2</sub> possesses a band gap in the infrared region. Further, PtSe<sub>2</sub> can be synthesized at low temperatures and has proven to be relatively air stable, both prerequisites for most applications. Achieving a high film quality is crucial in order to maximize the performance of devices such as chemical sensors [1], IR-Photodetectors [2] or pressure sensors [3].

Here we present a detailed Raman and XPS characterization of grown PtSe<sub>2</sub> thin films. Wafer scale synthesis of PtSe<sub>2</sub> was achieved through selenization of pre-deposited platinum thin films by Thermally Assisted Conversion (TAC) using a custom designed reactor. The growth was carried out at temperatures between 400 °C and 600 °C on various substrates with selenium as a solid state precursor. Synthesis optimization shows a high dependence of the film quality on the process parameters. With carefully defined metrics for Raman and XPS measurements minor variations in quality and structural composition of the PtSe<sub>2</sub> films can be identified [4]. This precise quality assessment of PtSe<sub>2</sub> is a step forward in the development of 2D materials based hybrid devices.

## References

- [1] C. Yim et al., ACS Nano, 10 (2016), 9550
- [2] C. Yim et al., Nano Lett, 3 (2018), 1794
- [3] S. Wagner et al., Nano Lett., 6 (2018), 3768
- [4] S.Lukas et al., Adv.Funct.Mater. 31 (2021), 2102929

## Figures



**Figure 1:** a) Direct selenization of pre-deposited Platinum layers. b) PtSe<sub>2</sub> thin films on SiO<sub>2</sub>/Si. c) Raman spectra of the selenized PtSe<sub>2</sub> films. The varying quality of all successful converted films is evident in the statistical analysis of Raman mapping.